

Product Summary

BV _{DSS}	R _{DS(on)}	I _D T _A = +25°C
-20V	0.75Ω @ V _{GS} = -4.5V	-1.03A
	1.05Ω @ V _{GS} = -2.5V	-0.7A

Features and Benefits

- Dual P-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMG1023UVQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

Description and Applications

This new generation MOSFET is designed to minimize on-state resistance (R_{DS(on)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- DC-DC Converters
- Load Switch
- Power Management Functions

Mechanical Data

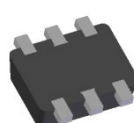
- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 Ⓔ3
- Weight: 0.006 grams (Approximate)



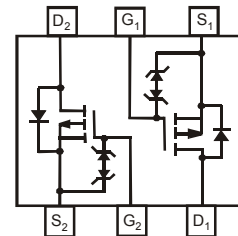
ESD PROTECTED



Top View



Bottom View



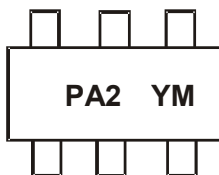
Top View

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG1023UVQ-7	SOT563	3,000/Tape & Reel
DMG1023UVQ-13	SOT563	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



PA2 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: 1 = 2021)
 M = Month (ex: 9 = September)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	H	I	J	K	L	M	N	O	P	R	S
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	± 6	V
Continuous Drain Current (Note 5) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	-1.03	A
		$T_A = +70^\circ\text{C}$		-0.68	
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)			I_{DM}	-3	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	Steady State	P_D	0.53	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	235	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Note: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-100	nA	V _{DS} = -20V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	—	—	±2.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	V _{GS(th)}	-0.5	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA	
Static Drain-Source On-Resistance	R _{DS(on)}	—	0.5	0.75	Ω	V _{GS} = -4.5V, I _D = -430mA	
			0.7	1.05			V _{GS} = -2.5V, I _D = -300mA
			1.0	1.5			V _{GS} = -1.8V, I _D = -150mA
			—	20			V _{GS} = -1.7V, I _D = -100mA
			—	25			V _{GS} = -1.5V, I _D = -100mA
Diode Forward Voltage	V _{SD}	—	-0.8	-1.2	V	V _{GS} = 0V, I _S = -150mA	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	—	59	—	pF	V _{DS} = -16V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	C _{OSS}	—	12	—	pF		
Reverse Transfer Capacitance	C _{rSS}	—	6.4	—	pF		
Total Gate Charge	Q _g	—	622	—	pC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -250mA	
Gate-Source Charge	Q _{gs}	—	100	—	pC		
Gate-Drain Charge	Q _{gd}	—	132	—	pC		
Turn-On Delay Time	t _{D(on)}	—	5.1	—	ns	V _{DD} = -10V, V _{GS} = -4.5V, R _L = 47Ω, R _G = 10Ω, I _D = -200mA	
Turn-On Rise Time	t _R	—	8.1	—	ns		
Turn-Off Delay Time	t _{D(off)}	—	28.4	—	ns		
Turn-Off Fall Time	t _F	—	20.7	—	ns		

Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to production testing.

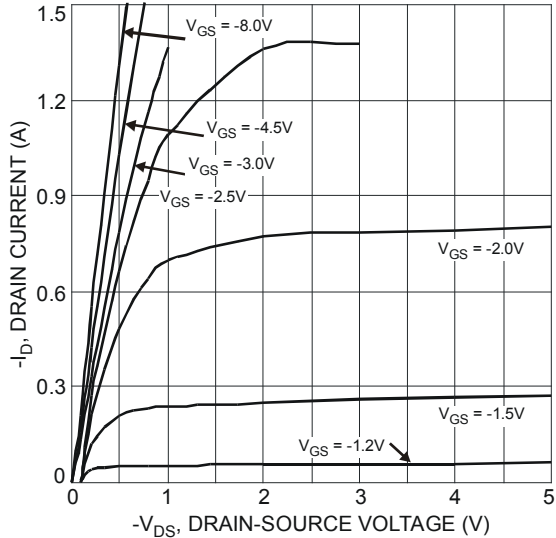


Fig. 1 Typical Output Characteristic

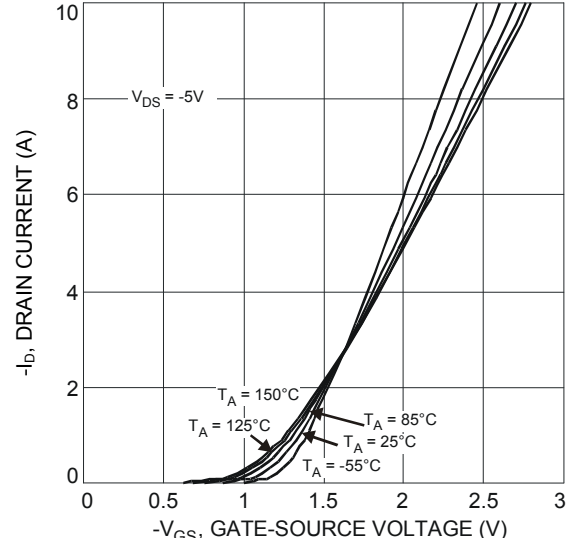


Fig. 2 Typical Transfer Characteristic

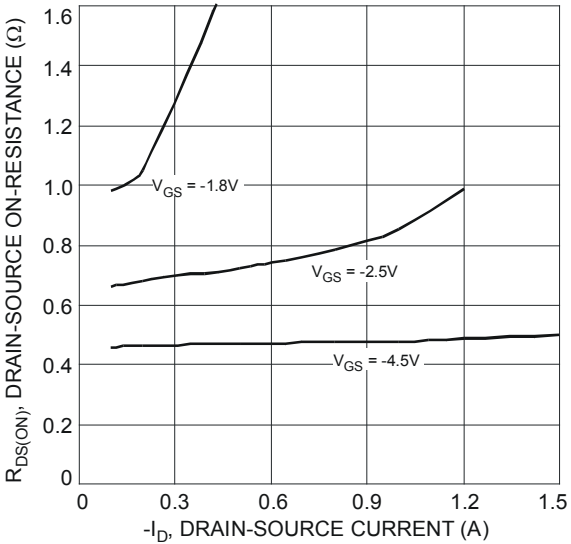


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

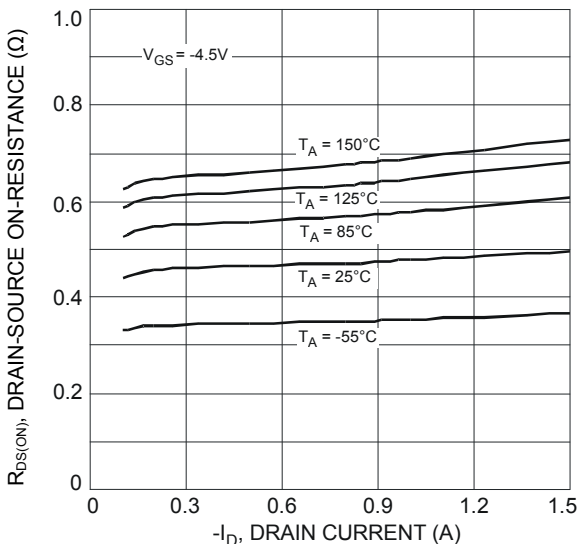


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

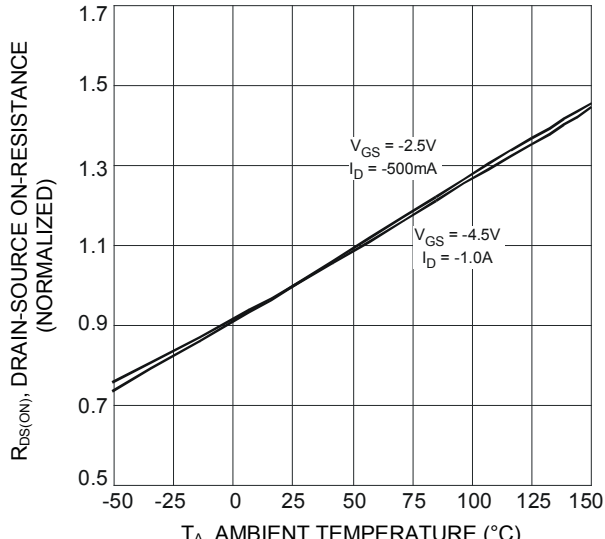


Fig. 5 On-Resistance Variation with Temperature

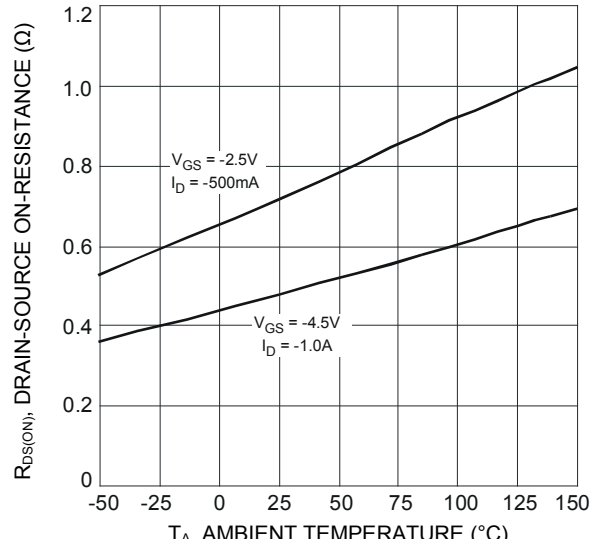


Fig. 6 On-Resistance Variation with Temperature

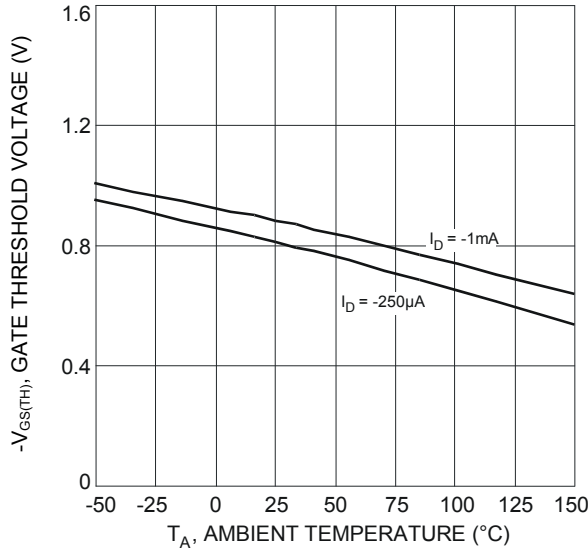


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

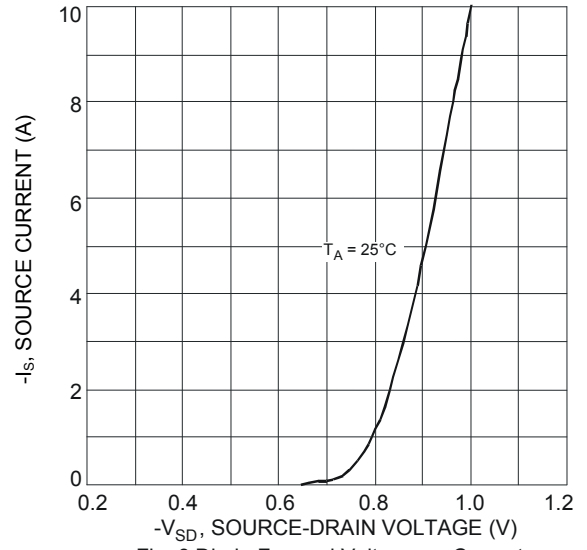


Fig. 8 Diode Forward Voltage vs. Current

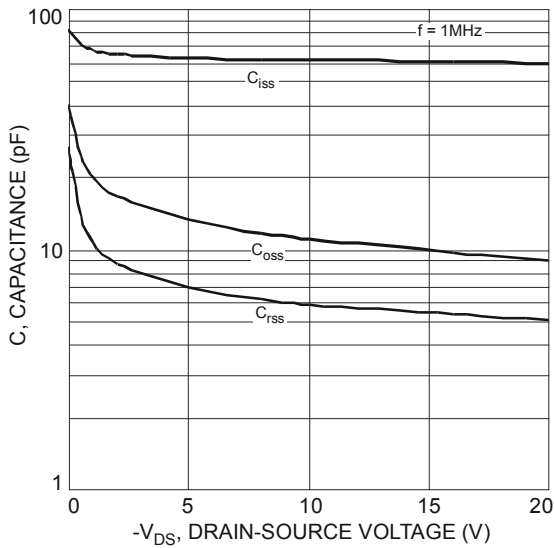


Fig. 9 Typical Total Capacitance

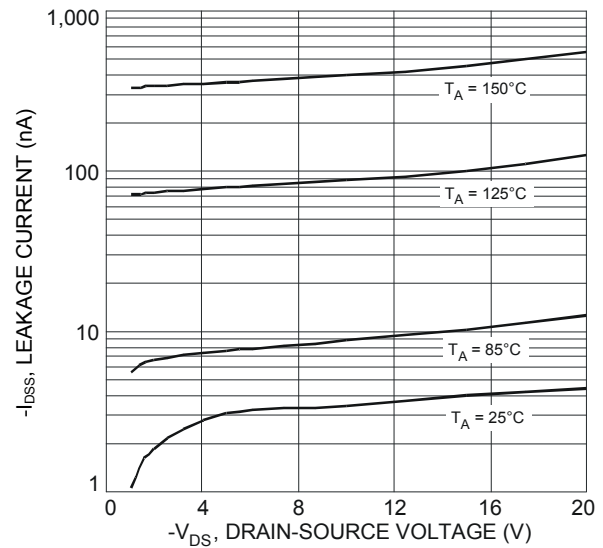


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

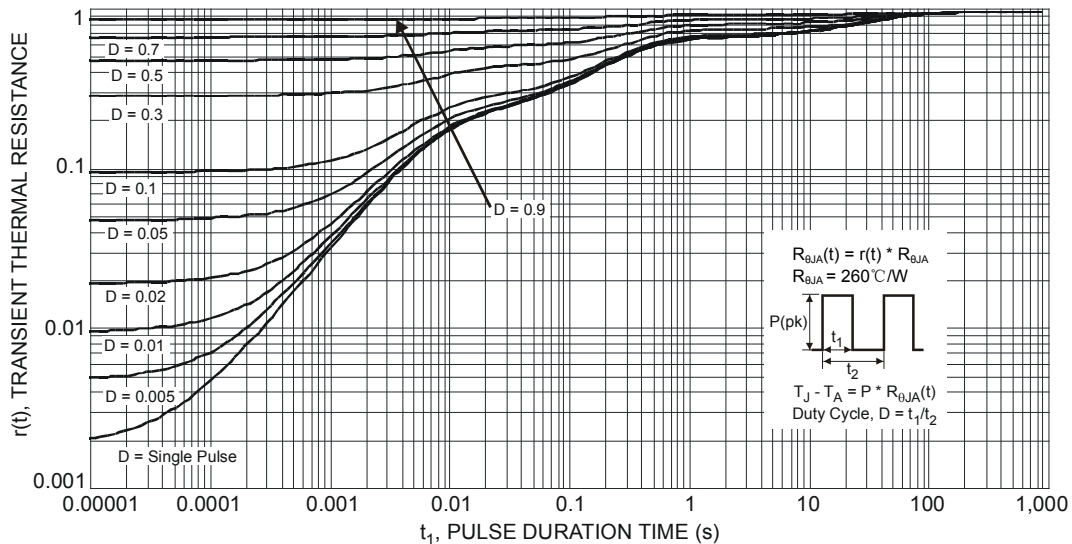
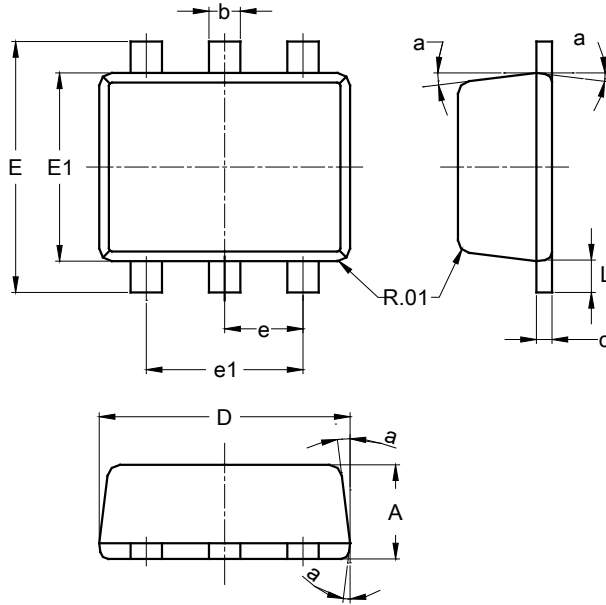


Fig. 11 Transient Thermal Response

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT563

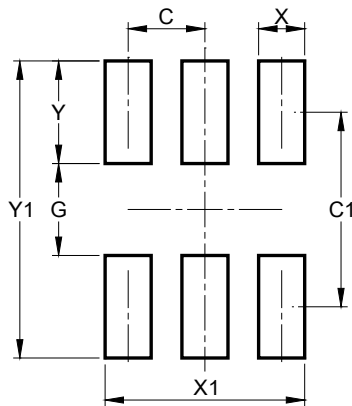


SOT563			
Dim	Min	Max	Typ
A	0.55	0.60	--
b	0.15	0.30	0.20
c	0.10	0.18	0.11
D	1.50	1.70	1.60
E	1.55	1.70	1.60
E1	1.10	1.25	1.20
e	--	--	0.50
e1	0.90	1.10	1.00
L	0.10	0.30	0.20
a	8°	9°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT563



Dimensions	Value (in mm)
C	0.500
C1	1.270
G	0.600
X	0.300
X1	1.300
Y	0.670
Y1	1.940

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